

Advance Technical Information

PolarP2™ **Power MOSFET**

IXTQ470P2

N-Channel Enhancement Mode Avalanche Rated Fast Intrinsic Diode

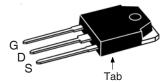


$V_{\scriptscriptstyle \sf DSS}$	=	500V
 D25	=	42A
R _{DS(on)}	≤	$145 \mathrm{m}\Omega$
t _{rr(typ)}	=	400ns

Symbol	Test Conditions	Maximum Ratings		
V _{DSS} V _{DGR}	$T_J = 25^{\circ}\text{C} \text{ to } 150^{\circ}\text{C}$ $T_J = 25^{\circ}\text{C} \text{ to } 150^{\circ}\text{C}, R_{GS} = 1\text{M}\Omega$	500 500	V	
V _{GSS}	Continuous Transient	± 30 ± 40	V	
I _{D25}	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 25^{\circ}{\rm C}$, Pulse Width Limited by $T_{\rm JM}$	42 126	A A	
I _A E _{AS}	T _C = 25°C T _C = 25°C	42 1.3	A J	
dv/dt	$I_{_{S}} \le I_{_{DM}}, \ V_{_{DD}} \le V_{_{DSS}}, T_{_{J}} \le 150^{\circ}C$	10	V/ns	
P_{D}	T _c = 25°C	830	W	
T _J T _{JM} T _{stg}		-55 +150 150 -55 +150	°C °C °C	
T _L T _{SOLD}	Maximum Lead Temperature for Soldering Plastic Body for 10s	300 260	°C °C	
M _d	Mounting Torque	1.13/10	Nm/lb.in.	
Weight		5.5	g	

V _{DSS}	$T_{\perp} = 25^{\circ}C \text{ to } 150^{\circ}C$	500	V
V _{DGR}	$T_J^{\circ} = 25^{\circ}\text{C} \text{ to } 150^{\circ}\text{C}, R_{gs} = 1\text{M}\Omega$	500	V
V _{GSS}	Continuous	± 30	V
V _{GSM}	Transient	± 40	V
I _{D25}	T _C = 25°C	42	Α
I _{DM}	$T_{\rm C}^{\circ}$ = 25°C, Pulse Width Limited by $T_{\rm JM}$	126	Α
I,	T _C = 25°C	42	Α
I _A E _{AS}	$T_{c}^{\circ} = 25^{\circ}C$	1.3	J
dv/dt	$I_{_{S}} \le I_{_{DM}}, \ V_{_{DD}} \le V_{_{DSS}}, T_{_{J}} \le 150^{\circ}C$	10	V/ns
P_{D}	T _C = 25°C	830	W
T		-55 +150	°C
T _{JM}		150	°C
T _{stg}		-55 +150	°C
T,	Maximum Lead Temperature for Soldering	300	°C
T	Plastic Body for 10s	260	°C

TO-3P



G = Gate= Drain D S = Source Tab = Drain

Features

- Avalanche Rated
- Fast Intrinsic Diode
- Dynamic dv/dt Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode **Power Supplies**
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

		Chara Min.	acteristic Values Typ. Max.		
BV _{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	500			V
$V_{\rm GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2.5		4.5	V
l _{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 100	nA
I _{DSS}	$V_{DS} = V_{DSS}, V_{GS} = 0V$			5	μΑ
	$T_J = 125^{\circ}C$			50	μΑ
R _{DS(on)}	$V_{GS} = 10V, I_{D} = 0.5 \bullet I_{D25}, \text{ Note 1}$			145	mΩ

TO-3P (IXTQ) Outline



SymbolTest ConditionsCharacteristic Value $(T_J = 25^{\circ}\text{C Unless Otherwise Specified})$ Min. Typ.		Values Max.		
g _{fs}	V _{DS} = 20V, I _D = 0.5 • I _{D25} , Note 1	23	36	S
C _{iss}			5400	pF
C _{oss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		545	pF
C _{rss}			44	pF
t _{d(on)}	Resistive Switching Times		23	ns
t,	$V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_{D} = 0.5 \cdot I_{D25}$		12	ns
t _{d(off)}			42	ns
t _f	$R_{_{G}} = 3\Omega \text{ (External)}$		9	ns
$Q_{g(on)}$			88	nC
Q _{gs}	$V_{GS} = 10V$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_{D} = 0.5 \cdot I_{D25}$		30	nC
Q_{gd}	a _{gd}		31	nC
R _{thJC}				0.15 °C/W
$\mathbf{R}_{\mathrm{thCS}}$			0.25	°C/W

Pins: 1 - Gate 2 - Drain 3 - Source 4 - Drain SYM MIN MAX MIN MAX A .185 .193 4.70 4.90 A1 .051 .059 1.30 1.50 A2 .057 .065 1.45 1.65 b .035 .045 0.90 1.15 b2 .075 .087 1.90 2.20 b4 .114 .126 2.90 3.20 c .022 .031 0.55 0.80 D .780 .791 19.80 20.10 D1 .665 .677 16.90 17.20 E .610 .622 15.50 15.80 E1 .531 .539 13.50 13.70 e .215 BSC 5.45 BSC L .779 .795 19.80 20.20 L1 .134 .142 3.40 3.60 ØP 1.26 .134 3.20 3.40 ØP 1.26 .134 3.20 3.40 ØP 1.272 .280 6.90 7.10 S .193 .201 4.90 5.10 All metal area are tin plated.

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values			
$(T_J = 25^{\circ}C U)$	nless Otherwise Specified)	Min.	Тур.	Max.	
I _s	$V_{GS} = 0V$			42	Α
I _{SM}	Repetitive, Pulse Width Limited by $\rm T_{_{\rm JM}}$			168	Α
V _{SD}	$I_F = I_S$, $V_{GS} = 0V$, Note 1			1.5	V
t _{rr}	$I_{F} = 21A, -di/dt = 100A/\mu s$		400		ns
	$V_{R} = 100V, V_{GS} = 0V$				

Note 1. Pulse test, $t \le 300\mu s$, duty cycle, $d \le 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.